



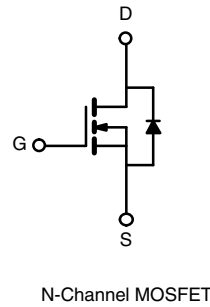
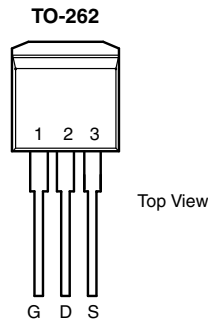
Automotive N-Channel 100 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V _{DS} (V)	100
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.0038
I _D (A)	120
Configuration	Single

FEATURES

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified^d
- 100 % R_g and UIS Tested
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912



ORDERING INFORMATION	
Package	TO-262
Lead (Pb)-free and Halogen-free	SQV120N10-3m8-GE3

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V _{DS}	100	V	
Gate-Source Voltage	V _{GS}	± 20		
Continuous Drain Current	I _D	T _C = 25 °C ^a	120	
		T _C = 125 °C	102	
Continuous Source Current (Diode Conduction) ^a	I _S	120	A	
Pulsed Drain Current ^b	I _{DM}	480		
Single Pulse Avalanche Current	I _{AS}	73		
Single Pulse Avalanche Energy	E _{AS}	L = 0.1 mH	266	mJ
Maximum Power Dissipation ^b			T _C = 25 °C	
		T _C = 125 °C	83	W
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R _{thJA}	40	°C/W
Junction-to-Case (Drain)			

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).
- Parametric verification ongoing.



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA	100	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.5	3.0	3.5	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 100 V	-	-	1	μA
		V _{GS} = 0 V, V _{DS} = 100 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V, V _{DS} = 100 V, T _J = 175 °C	-	-	500	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V, V _{DS} ≥ 5 V	120	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A	-	0.0030	0.0038	Ω
		V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C	-	-	0.0064	
		V _{GS} = 10 V, I _D = 20 A, T _J = 175 °C	-	-	0.0080	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 20 A	-	82	-	S
Dynamic^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz	-	5780	7230	pF
Output Capacitance	C _{oss}		-	3070	3840	
Reverse Transfer Capacitance	C _{rss}		-	305	385	
Total Gate Charge ^c	Q _g	V _{GS} = 10 V, V _{DS} = 50 V, I _D = 70 A	-	125	190	nC
Gate-Source Charge ^c	Q _{gs}		-	28	-	
Gate-Drain Charge ^c	Q _{gd}		-	46	-	
Gate Resistance	R _g	f = 1 MHz	1.6	3.3	5	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 50 V, R _L = 0.7 Ω I _D ≅ 70 A, V _{GEN} = 10 V, R _g = 1 Ω	-	16	25	ns
Rise Time ^c	t _r		-	110	165	
Turn-Off Delay Time ^c	t _{d(off)}		-	40	60	
Fall Time ^c	t _f		-	12	20	
Source-Drain Diode Ratings and Characteristics^b						
Pulsed Current ^a	I _{SM}		-	-	480	A
Forward Voltage	V _{SD}	I _F = 100 A, V _{GS} = 0	-	0.9	1.5	V

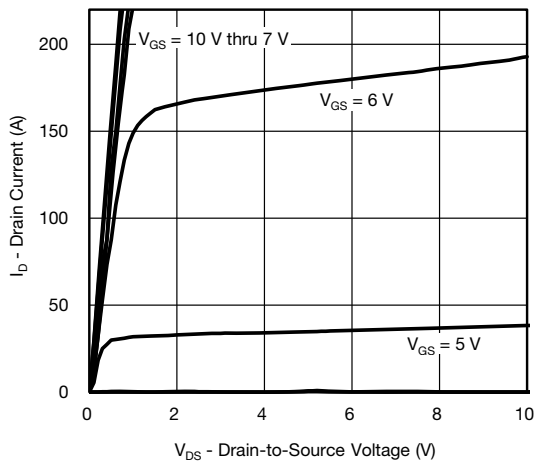
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

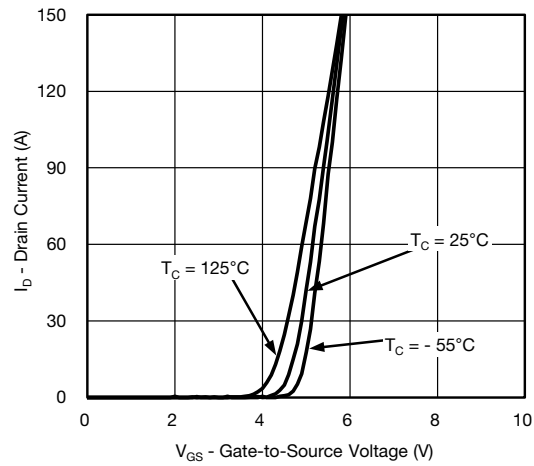
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



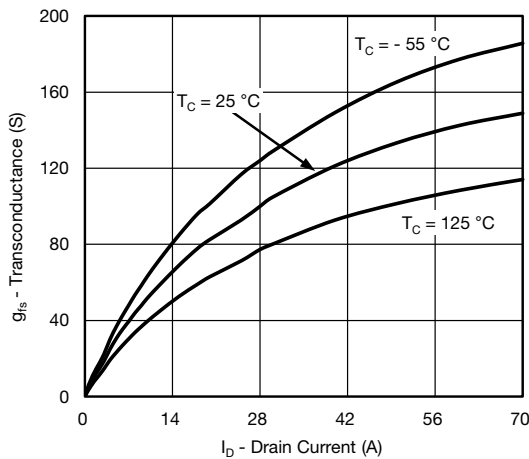
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



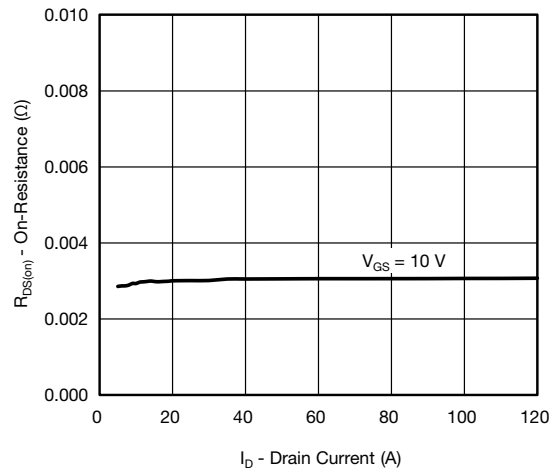
Output Characteristics



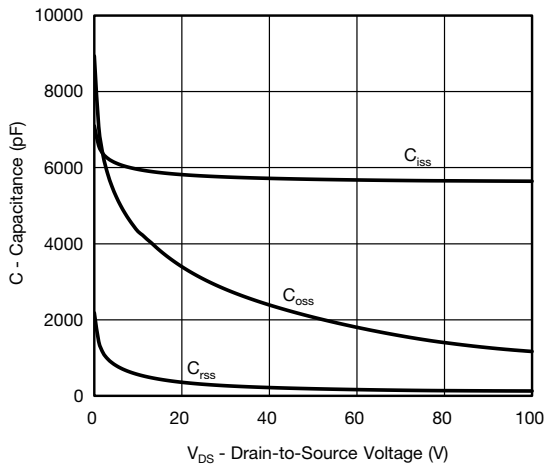
Transfer Characteristics



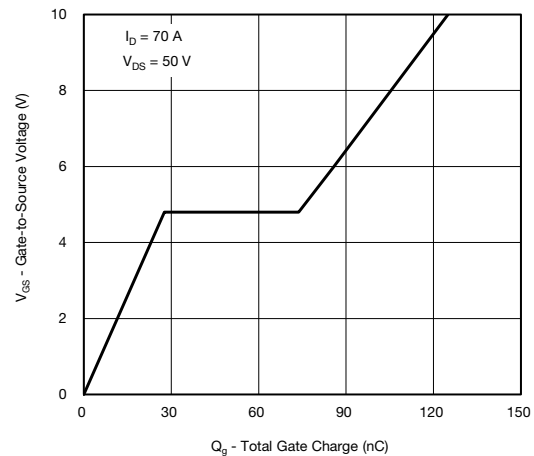
Transconductance



On-Resistance vs. Drain Current



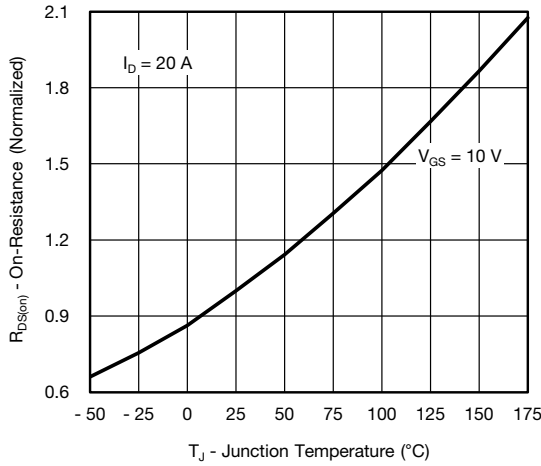
Capacitance



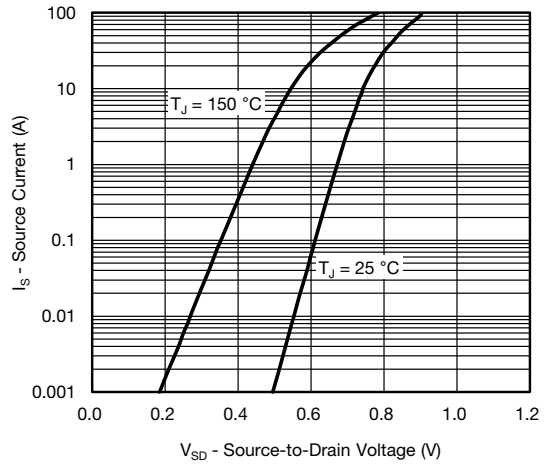
Gate Charge



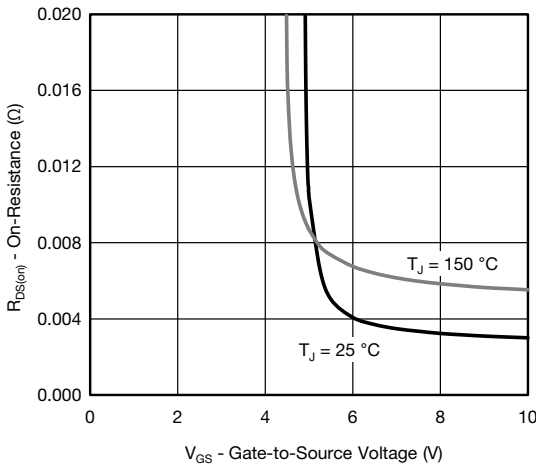
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



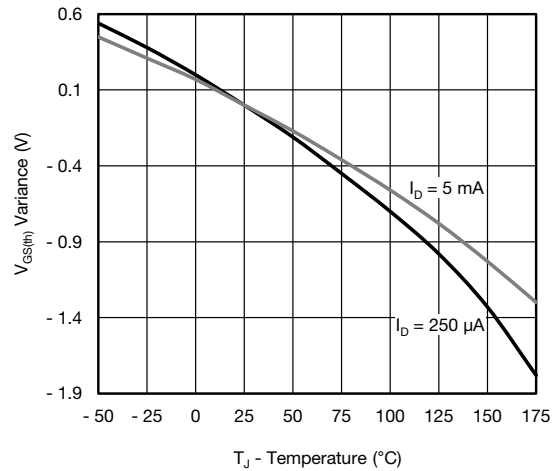
On-Resistance vs. Junction Temperature



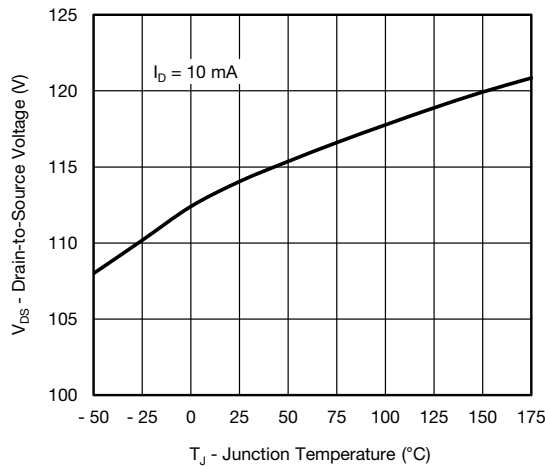
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



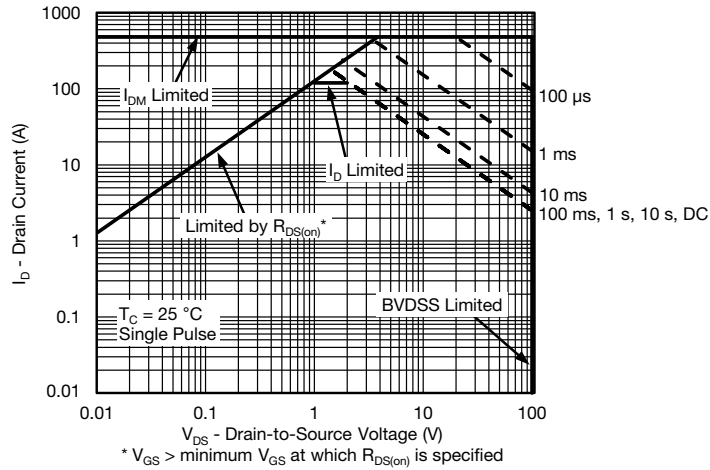
Threshold Voltage



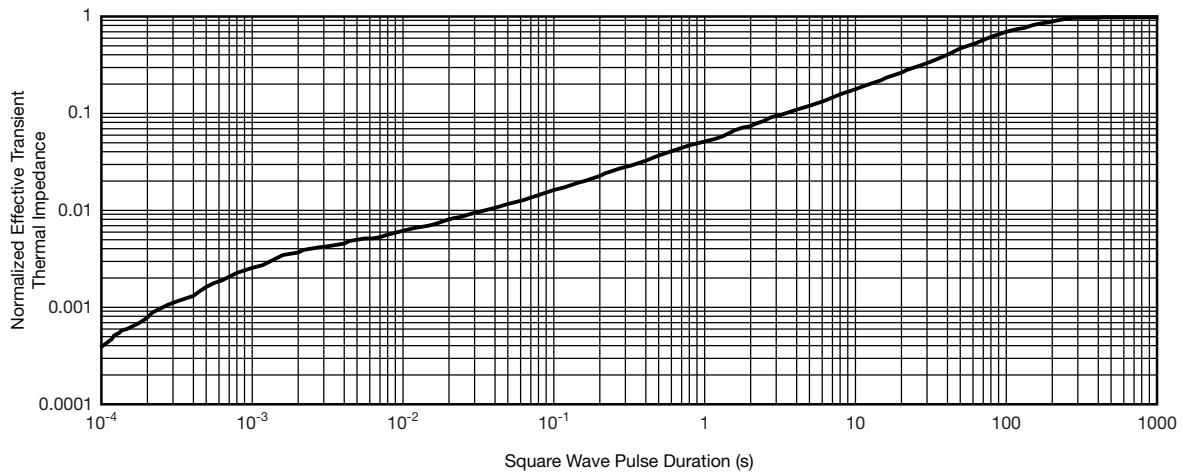
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



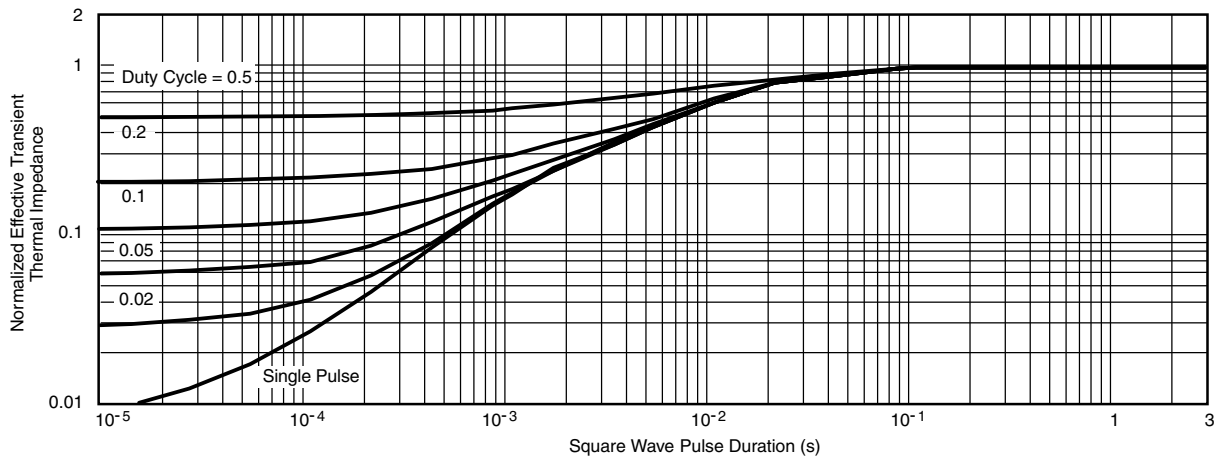
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



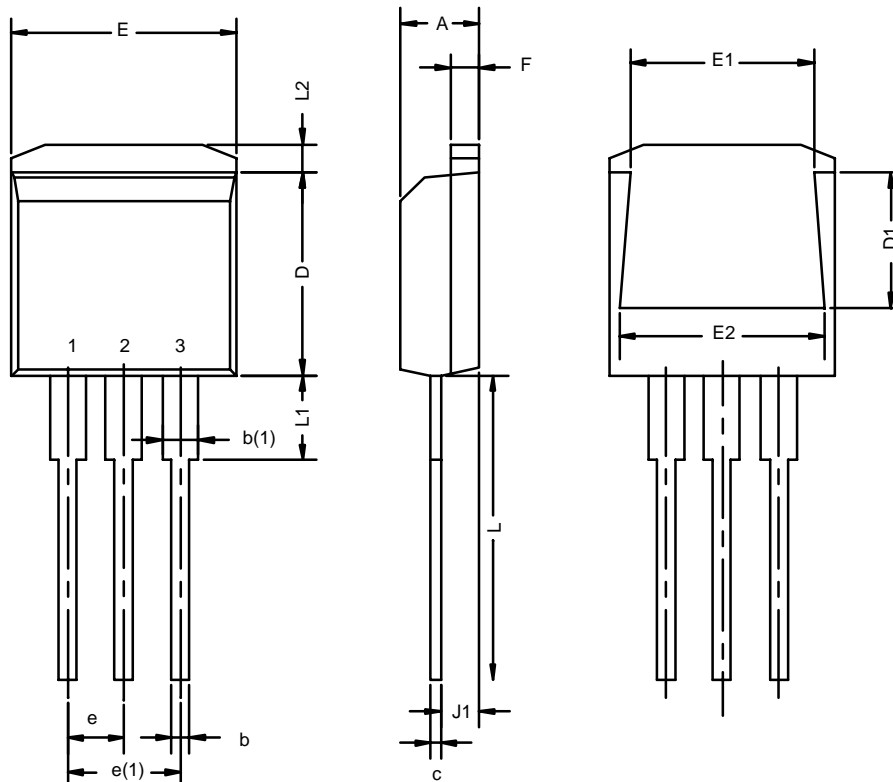
Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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TO-262: 3-LEAD



Dim	MILLIMETERS*		INCHES	
	Min	Max	Min	Max
A	4.32	4.70	0.170	0.185
b	0.64	1.00	0.025	0.039
b(1)	1.14	1.40	0.045	0.055
c	0.36	0.50	0.014	0.020
D	8.64	9.65	0.340	0.380
D1	5.59	6.10	0.220	0.240
e	2.41	2.67	0.095	0.105
e(1)	4.95	5.33	0.195	0.210
E	10.03	10.41	0.395	0.410
E1	7.87	8.64	0.310	0.340
E2	9.02	9.53	0.355	0.375
F	1.14	1.40	0.045	0.055
J1	2.41	2.79	0.095	0.110
L	13.08	14.22	0.515	0.560
L1	-	3.81	-	0.150
L2	1.02	1.40	0.040	0.055

ECN: T-02234—Rev. C, 14-Oct-02
DWG: 5855

*Use millimeters as the primary measurement



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